

TPS7B81 150mA、40V、超低 I_Q 、低ドロップアウト・レギュレータ

1 特長

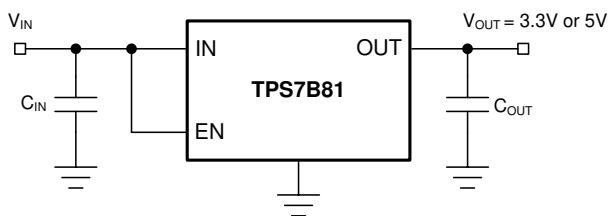
- 広い入力電圧範囲：3V～40V
- 出力電流：150mA
- 非常に低い静止電流 (I_Q)
 - 軽負荷時: 2.7 μ A (標準値)
 - 軽負荷時: 4.5 μ A (最大値)
- 精度：ライン、負荷、温度の範囲全体にわたって 1.5% の誤差
- ドロップアウト電圧：100mA で 180mV (標準値)
- 広いイネーブル電圧範囲：2V～ V_{IN} (最高 40V)
- 入力電圧過渡の許容値：45V
- 5V および 3.3V 固定出力電圧オプション
- 電流制限およびサーマル・シャットダウン保護
- 広い範囲のコンデンサで安定 (1 μ F～200 μ F) ⁽¹⁾
- 接合部温度範囲：-40°C～+150°C
- 熱性能の高いパッケージ
 - DGN (8 ピン HVSSOP)、 $R_{\theta JA} = 63.9^\circ\text{C/W}$
 - DRV (6 ピン WSON)、 $R_{\theta JA} = 72.8^\circ\text{C/W}$

(1) 出力コンデンサの要件については、「推奨動作条件」表を参照してください。

2 アプリケーション

- 煙 / 熱検知器
- サーモスタット
- モーション検出器 (PIR、uWave など)
- コードレス電動工具
- 家電機器用バッテリー・パック
- モータ・ドライブ

代表的なアプリケーションの回路図



3 説明

TPS7B81 は、最高 40V の入力電圧で動作し、最大 150mA の電流を供給できる低ドロップアウト (LDO) リニア・レギュレータです。軽負荷時の静止電流がわずか 2.7 μ A であるため、入力電源電圧範囲の広い設計や、スタンバイ時消費電力が非常に小さいことが要求される多セル・バッテリー駆動アプリケーションに最適です。45V の過渡電圧に耐えられるので、誘導性キックバックが発生する可能性があるアプリケーションでヘッドルームが増え、電圧抑制のための外付け回路を減らすことができます。

TPS7B81 には短絡および過電流制限機能が内蔵されているため、フォルト状態でもシステムを保護できます。スタンバイ時の消費電力が小さいことに加えて、軽負荷時のドロップアウト電圧が非常に小さいため、消耗したバッテリーで動作する場合でもレギュレーションを維持できます。

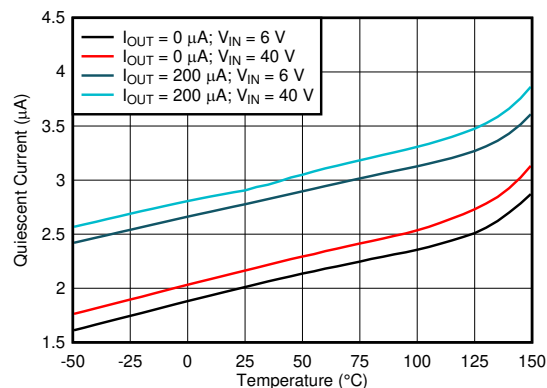
TPS7B81 は、熱的に強化された 8 ピンの HVSSOP および 6 ピンの WSON パッケージで供給されます。どちらのパッケージも熱伝導性が高くサイズが小さいため、小型の設計が可能であり、電動工具、モーター・ドライブ・モジュール、バッテリー・パックなど、スペースの制約が厳しいアプリケーションに適しています。

製品情報⁽¹⁾

型番	パッケージ	本体サイズ(公称)
TPS7B81	HVSSOP (8)	3.00mm×3.00mm
	WSON (6)	2.00mm × 2.00mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

静止電流と周囲温度の関係
($V_{OUT} = 3.3V$)



目次

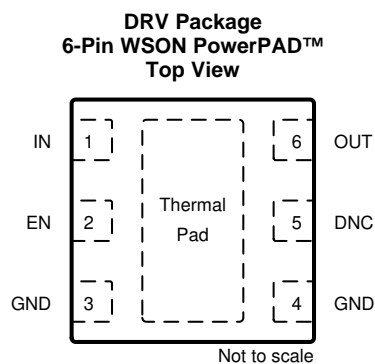
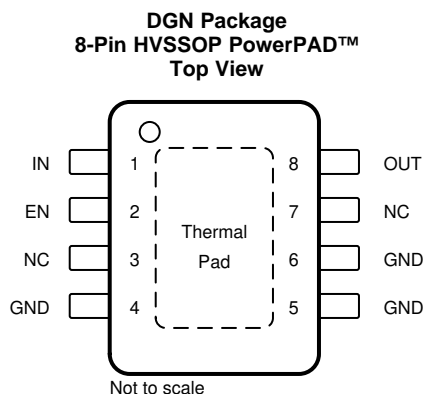
1	特長	1	7.4	Device Functional Modes.....	11
2	アプリケーション.....	1	8	Application and Implementation	12
3	説明.....	1	8.1	Application Information.....	12
4	改訂履歴.....	2	8.2	Typical Application	15
5	Pin Configuration and Functions	3	9	Power Supply Recommendations	16
6	Specifications	4	10	Layout	17
6.1	Absolute Maximum Ratings	4	10.1	Layout Guidelines	17
6.2	ESD Ratings.....	4	10.2	Layout Example	17
6.3	Recommended Operating Conditions.....	4	11	デバイスおよびドキュメントのサポート	18
6.4	Thermal Information	4	11.1	ドキュメントの更新通知を受け取る方法.....	18
6.5	Electrical Characteristics.....	5	11.2	サポート・リソース.....	18
6.6	Typical Characteristics.....	6	11.3	商標	18
7	Detailed Description	10	11.4	静電気放電に関する注意事項	18
7.1	Overview	10	11.5	Glossary	18
7.2	Functional Block Diagram	10	12	メカニカル、パッケージ、および注文情報	18
7.3	Feature Description.....	10			

4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

日付	リビジョン	注
2020 年 4 月	*	初版

5 Pin Configuration and Functions



Pin Functions

NAME	PIN NO.		I/O	DESCRIPTION
	NO.			
	DGN	DRV		
DNC	—	5	—	Do not connect to a biased voltage. Tie this pin to ground or leave floating.
EN	2	2	I	Enable input pin. Drive EN greater than V_{IH} to turn on the regulator. Drive EN less than V_{IL} to put the low-dropout (LDO) into shutdown mode.
GND	4, 5, 6	3,4	—	Ground reference
IN	1	1	I	Input power-supply pin. For best transient response and to minimize input impedance, use the recommended value or larger ceramic capacitor from IN to ground as listed in the Recommended Operating Conditions table and the Input Capacitor section. Place the input capacitor as close to the output of the device as possible.
NC	3, 7	—	—	Not internally connected
OUT	8	6	O	Regulated output voltage pin. A capacitor is required from OUT to ground for stability. For best transient response, use the nominal recommended value or larger ceramic capacitor from OUT to ground; see the Recommended Operating Conditions table and the Output Capacitor section. Place the output capacitor as close to output of the device as possible.
Thermal pad			—	Connect the thermal pad to a large-area GND plane for improved thermal performance.

6 Specifications

6.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted)⁽¹⁾⁽²⁾

		MIN	MAX	UNIT
V _{IN}	Unregulated input voltage ⁽³⁾	-0.3	45	V
V _{EN}	Enable input voltage ⁽³⁾	-0.3	V _{IN}	V
V _{OUT}	Regulated output	-0.3	7	V
T _J	Junction temperature	-40	150	°C
T _{stg}	Storage temperature	-40	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to GND.
- (3) Absolute maximum voltage, can withstand 45 V for 200 ms.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	

- (1) JEDEC document JEP155 states that 2-kV HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 500-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{IN}	Unregulated input voltage	3	40	V
V _{EN}	Enable input voltage	0	V _{IN}	V
C _{OUT}	Output capacitor requirements ⁽¹⁾	1	200	μF
ESR	Output capacitor ESR requirements ⁽²⁾	0.001	5	Ω
T _A	Ambient temperature	-40	125	°C
T _J	Junction temperature	-40	150	°C

- (1) The output capacitance range specified in the table is the effective capacitance value.
- (2) Relevant ESR value at f = 10 kHz

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS7B81		UNIT
		DGN (HVSSOP)	DRV (WSON)	
		8 PINS	6 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	63.9	72.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	50.2	85.8	°C/W
R _{θJB}	Junction-to-board thermal resistance	22.6	37.4	°C/W
ψ _{JT}	Junction-to-top characterization parameter	1.8	2.7	°C/W
ψ _{JB}	Junction-to-board characterization parameter	22.3	37.3	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	12.1	13.8	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics application report](#).

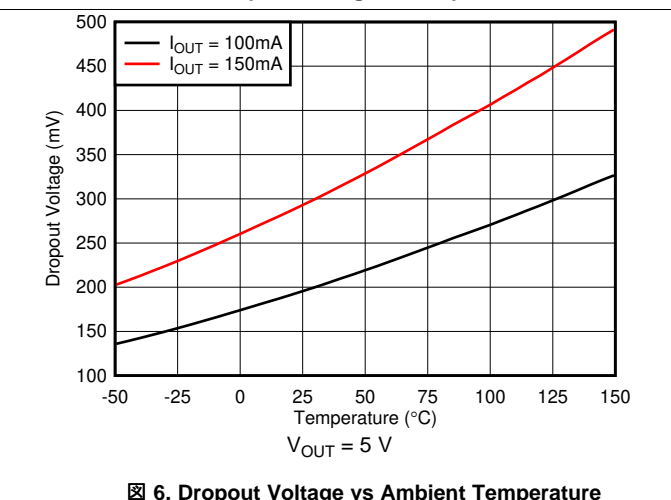
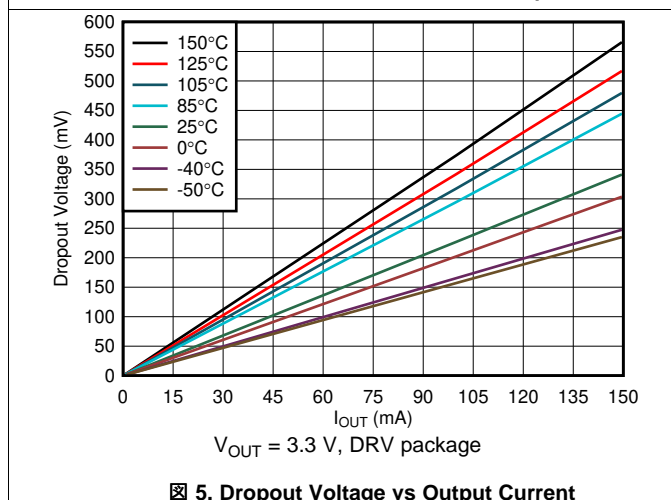
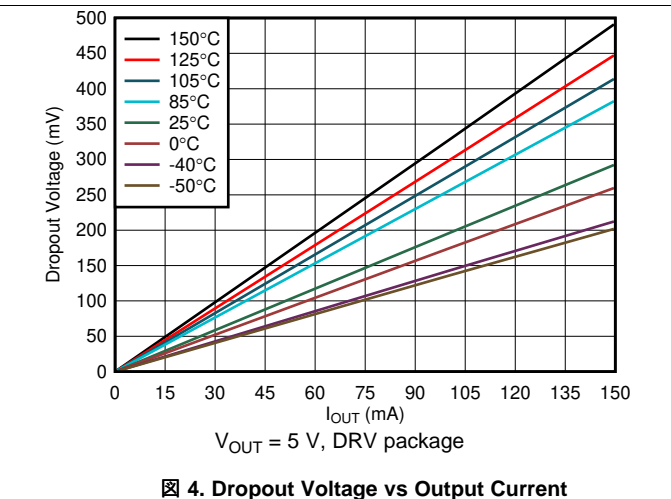
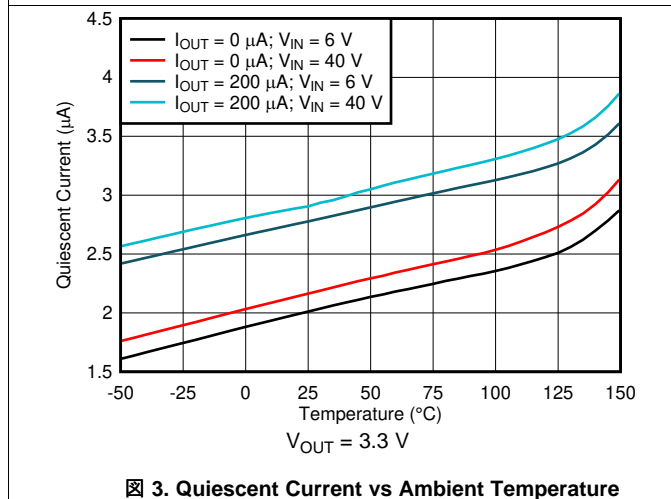
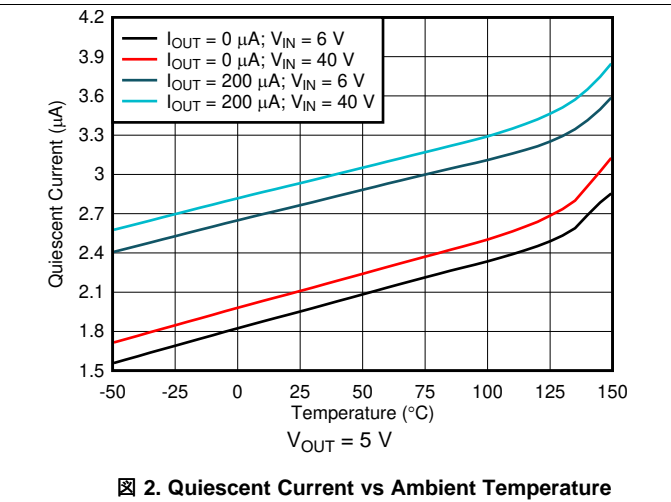
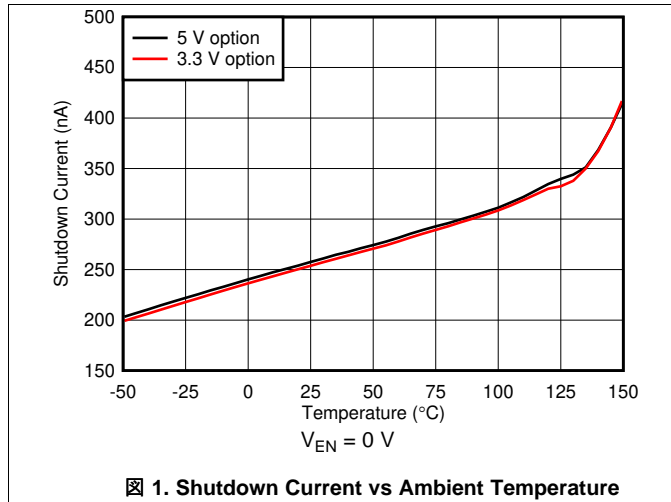
6.5 Electrical Characteristics

over operating ambient temperature range, $T_J = -40^{\circ}\text{C}$ to $+150^{\circ}\text{C}$, $V_{IN} = 14\text{ V}$, and $10\text{-}\mu\text{F}$ ceramic output capacitor (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
SUPPLY VOLTAGE AND CURRENT (IN)								
V_{IN}	Input voltage			$V_{OUT(Nom)} + V_{(Dropout)}$		40	V	
$I_{(SD)}$	Shutdown current	$EN = 0\text{ V}$		0.3	1		μA	
$I_{(Q)}$	Quiescent current	$V_{IN} = 6\text{ V to }40\text{ V}, EN \geq 2\text{ V}, I_{OUT} = 0\text{ mA}$		1.9	3.5		μA	
		$V_{IN} = 6\text{ V to }40\text{ V}, EN \geq 2\text{ V}, I_{OUT} = 0.2\text{ mA}$	DGN package	2.7	6.5			
			DRV package	2.7	4.5			
$V_{(IN, UVLO)}$	V_{IN} undervoltage detection	Ramp V_{IN} down until the output turns off				2.7	V	
		Hysteresis				200	mV	
ENABLE INPUT (EN)								
V_{IL}	Logic-input low level					0.7	V	
V_{IH}	Logic-input high level			2			V	
I_{EN}	Enable current			10			nA	
REGULATED OUTPUT (OUT)								
V_{OUT}	Regulated output	$V_{IN} = V_{OUT} + V_{(Dropout)}$ to 40 V , $I_{OUT} = 1\text{ mA to }150\text{ mA}$		-1.5%		1.5%		
$V_{(Line-Reg)}$	Line regulation	$V_{IN} = 6\text{ V to }40\text{ V}, I_{OUT} = 10\text{ mA}$				10	mV	
$V_{(Load-Reg)}$	Load regulation	$V_{IN} = 14\text{ V}, I_{OUT} = 1\text{ mA to }150\text{ mA}$		DGN package		20	mV	
				DRV package		10		
$V_{(Dropout)}$	Dropout voltage	$V_{OUT} = 5\text{ V}$	$I_{OUT} = 150\text{ mA}$	DGN package		270	540	mV
				DRV package		325	585	
			$I_{OUT} = 100\text{ mA}$	DGN package		180	350	
		DRV package		200	390			
		$V_{OUT} = 3.3\text{ V}$	$I_{OUT} = 150\text{ mA}$	DGN package		650		
				DRV package		345	675	
$I_{OUT} = 100\text{ mA}$					255	450		
I_{OUT}	Output current	V_{OUT} in regulation, $V_{IN} = 7\text{ V}$ for the fixed 5-V option, $V_{IN} = 5.8\text{ V}$ for the fixed 3.3-V option		0		150	mA	
$I_{(CL)}$	Output current limit	V_{OUT} short to $90\% \times V_{OUT}$		180	510	690	mA	
PSRR	Power-supply ripple rejection	$V_{(Ripple)} = 0.5\text{ V}_{PP}$, $I_{OUT} = 10\text{ mA}$, frequency = 100 Hz , $C_{OUT} = 2.2\text{ }\mu\text{F}$		60			dB	
OPERATING TEMPERATURE RANGE								
$T_{(SD)}$	Junction shutdown temperature			175			$^{\circ}\text{C}$	
$T_{(HYST)}$	Hysteresis of thermal shutdown			20			$^{\circ}\text{C}$	

6.6 Typical Characteristics

at $T_J = -40^{\circ}\text{C}$ to $+150^{\circ}\text{C}$, $V_{IN} = 14\text{ V}$, and $V_{EN} \geq 2\text{ V}$ (unless otherwise noted)



Typical Characteristics (continued)

at $T_J = -40^\circ\text{C}$ to $+150^\circ\text{C}$, $V_{IN} = 14\text{ V}$, and $V_{EN} \geq 2\text{ V}$ (unless otherwise noted)

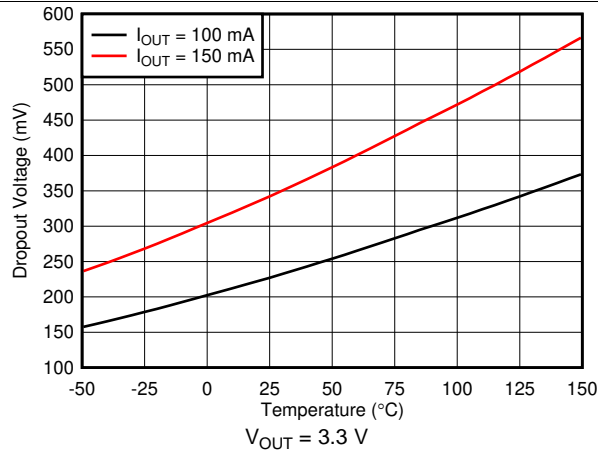


Figure 7. Dropout Voltage vs Ambient Temperature

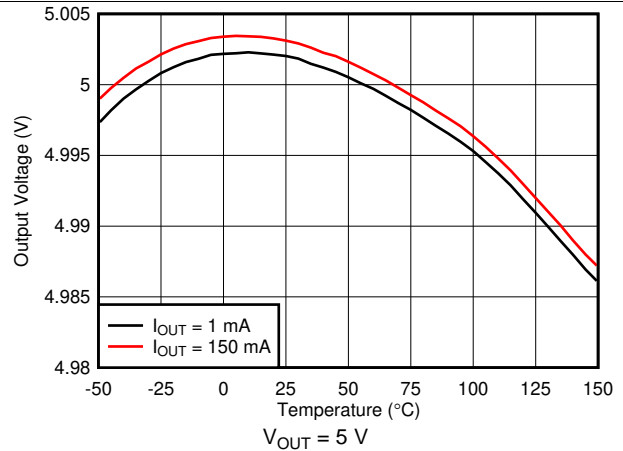


Figure 8. Output Voltage vs Ambient Temperature

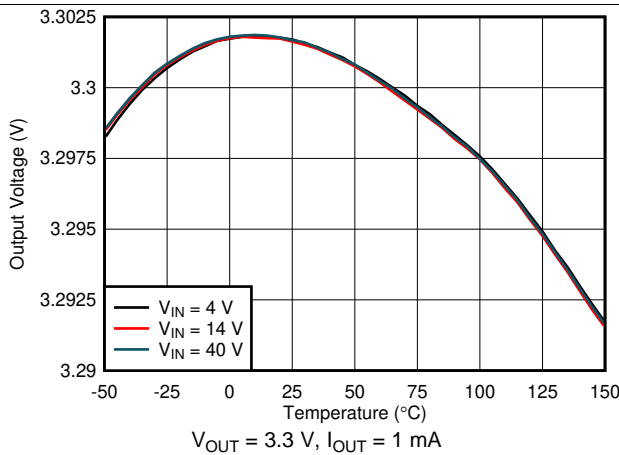
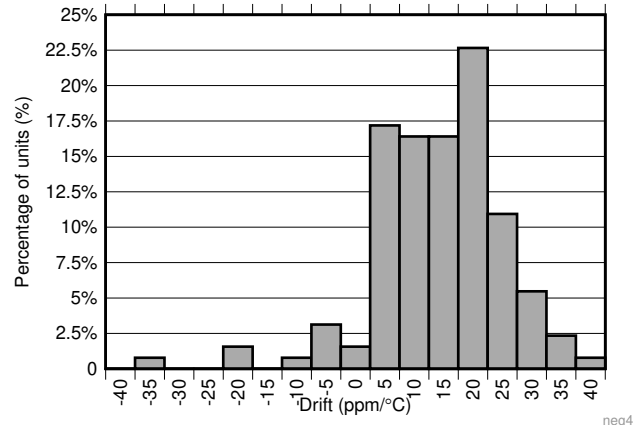
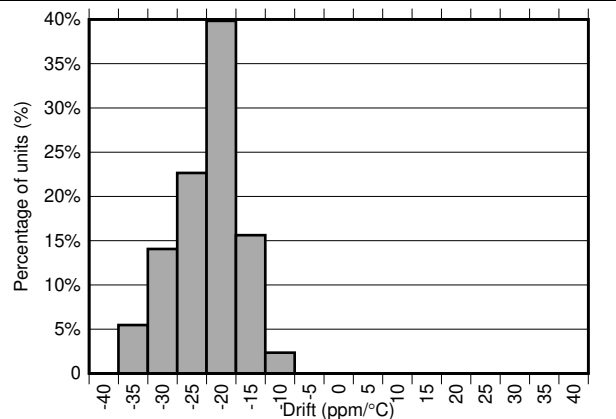


Figure 9. Output Voltage vs Ambient Temperature



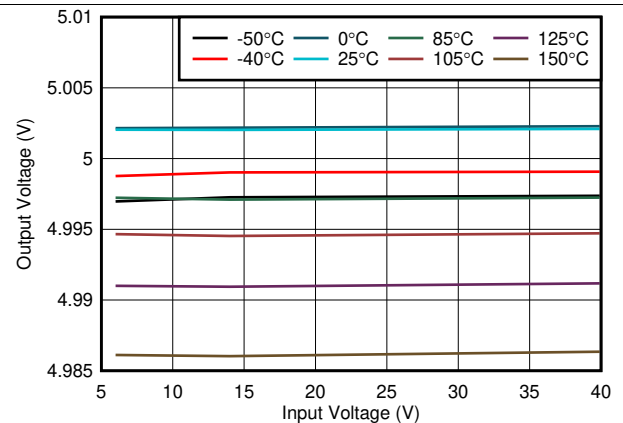
3.3-V and 5-V options, $I_{OUT} = 1\text{ mA}$

Figure 10. Temperature Drift Histogram (-40°C to $+25^\circ\text{C}$)



3.3-V and 5-V options, $I_{OUT} = 1\text{ mA}$

Figure 11. Temperature Drift Histogram (25°C to 150°C)

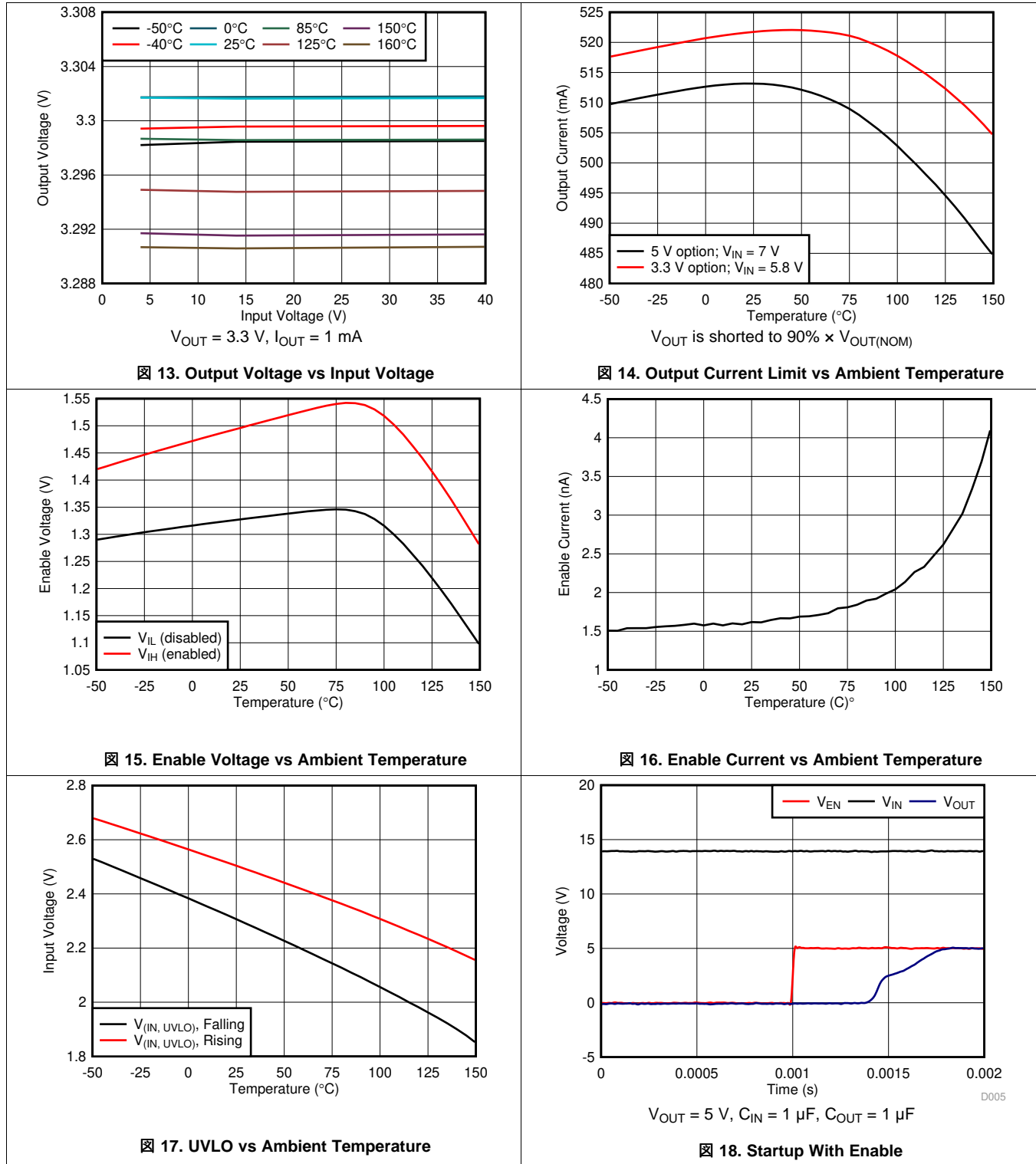


$V_{OUT} = 5\text{ V}$, $I_{OUT} = 1\text{ mA}$

Figure 12. Output Voltage vs Input Voltage

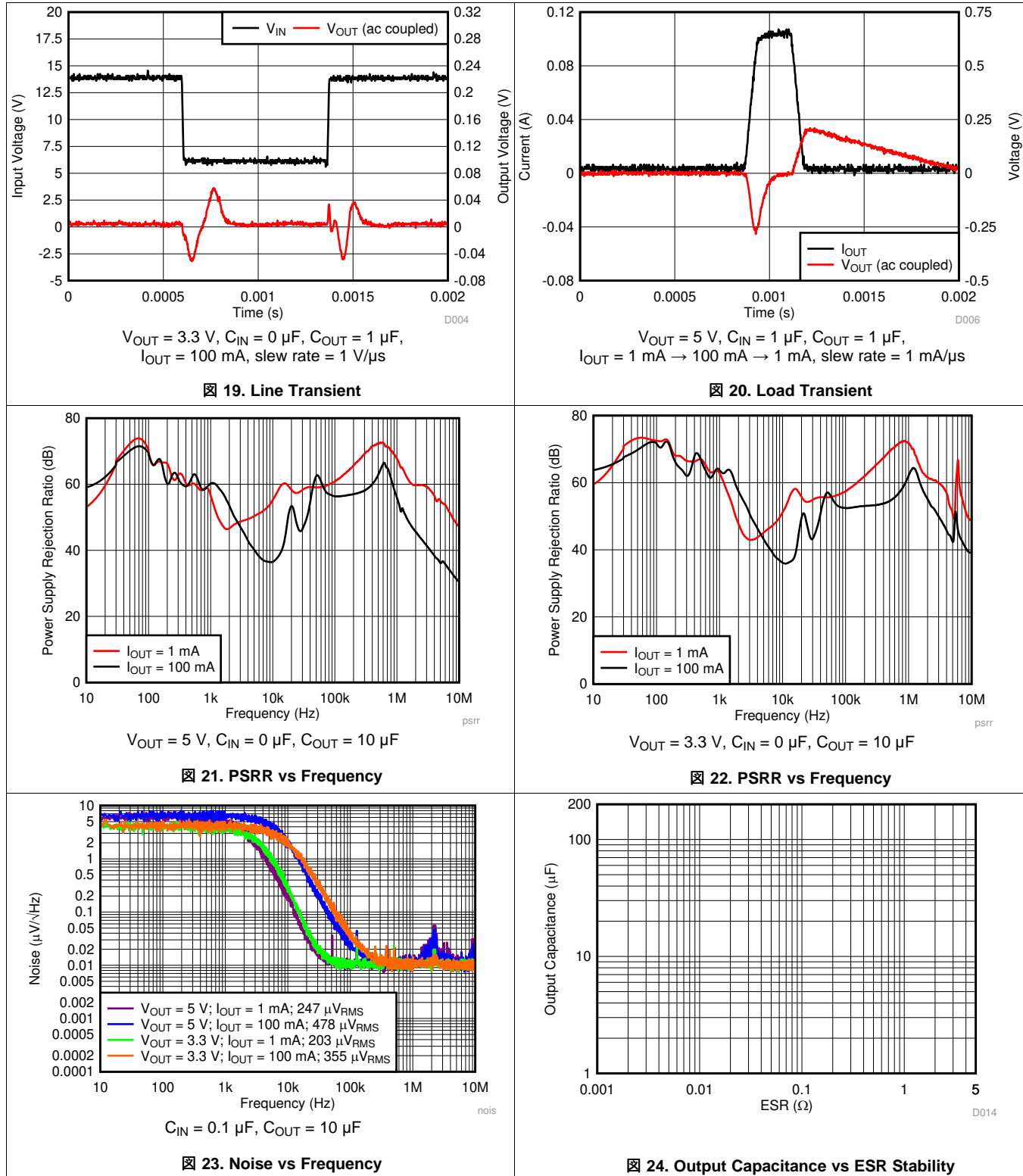
Typical Characteristics (continued)

at $T_J = -40^\circ\text{C}$ to $+150^\circ\text{C}$, $V_{IN} = 14\text{ V}$, and $V_{EN} \geq 2\text{ V}$ (unless otherwise noted)



Typical Characteristics (continued)

at $T_J = -40^{\circ}\text{C}$ to $+150^{\circ}\text{C}$, $V_{IN} = 14\text{ V}$, and $V_{EN} \geq 2\text{ V}$ (unless otherwise noted)



7.4 Device Functional Modes

7.4.1 Operation With V_{IN} Lower Than 3 V

The device normally operates with input voltages above 3 V. The device can also operate at lower input voltages; the maximum UVLO voltage is 2.7 V. The device does not operate at input voltages below the actual UVLO voltage.

7.4.2 Operation With V_{IN} Larger Than 3 V

When V_{IN} is greater than 3 V, if V_{IN} is also higher than the output set value plus the device dropout voltage, V_{OUT} is equal to the set value. Otherwise, V_{OUT} is equal to V_{IN} minus the dropout voltage.

表 1. Device Functional Mode Comparison

OPERATING MODE	PARAMETER			
Normal mode	$V_{IN} > V_{OUT(nom)} + V_{(Dropout)}$ and $V_{IN} \geq 3\text{ V}$	$V_{EN} > V_{IH}$	$I_{OUT} < I_{CL}$	$T_J < 160^\circ\text{C}$
Dropout mode	$3\text{ V} \leq V_{IN} < V_{OUT(nom)} + V_{(Dropout)}$	$V_{EN} > V_{IH}$	$I_{OUT} < I_{CL}$	$T_J < 160^\circ\text{C}$
Disabled mode (any true condition disables the device)	$V_{IN} < V_{(IN, UVLO)}$	$V_{EN} < V_{IL}$	—	$T_J > 160^\circ\text{C}$

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TPS7B81 is a 150-mA, 40-V, low-dropout (LDO) linear regulator with ultralow quiescent current. The PSpice transient model is available for download on the [product folder](#) and can be used to evaluate the basic functionality of the device.

8.1.1 Power Dissipation

Circuit reliability demands that proper consideration is given to device power dissipation, location of the circuit on the printed circuit board (PCB), and correct sizing of the thermal plane. The PCB area around the regulator must be as free as possible of other heat-generating devices that cause added thermal stresses.

As a first-order approximation, power dissipation in the regulator depends on the input-to-output voltage difference and load conditions. [式 1](#) approximates P_D :

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (1)$$

An important note is that power dissipation can be minimized, and thus greater efficiency achieved, by proper selection of the system voltage rails. Proper selection allows the minimum input-to-output voltage differential to be obtained. The low dropout of the device allows for maximum efficiency across a wide range of output voltages.

The main heat conduction path for the device is through the thermal pad on the package. As such, the thermal pad must be soldered to a copper pad area under the device. This pad area contains an array of plated vias that conduct heat to any inner plane areas or to a bottom-side copper plane.

The maximum power dissipation determines the maximum allowable junction temperature (T_J) for the device. According to [式 2](#), power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance ($R_{\theta JA}$) of the combined PCB, device package, and the temperature of the ambient air (T_A). This equation is rearranged for output current in [式 3](#).

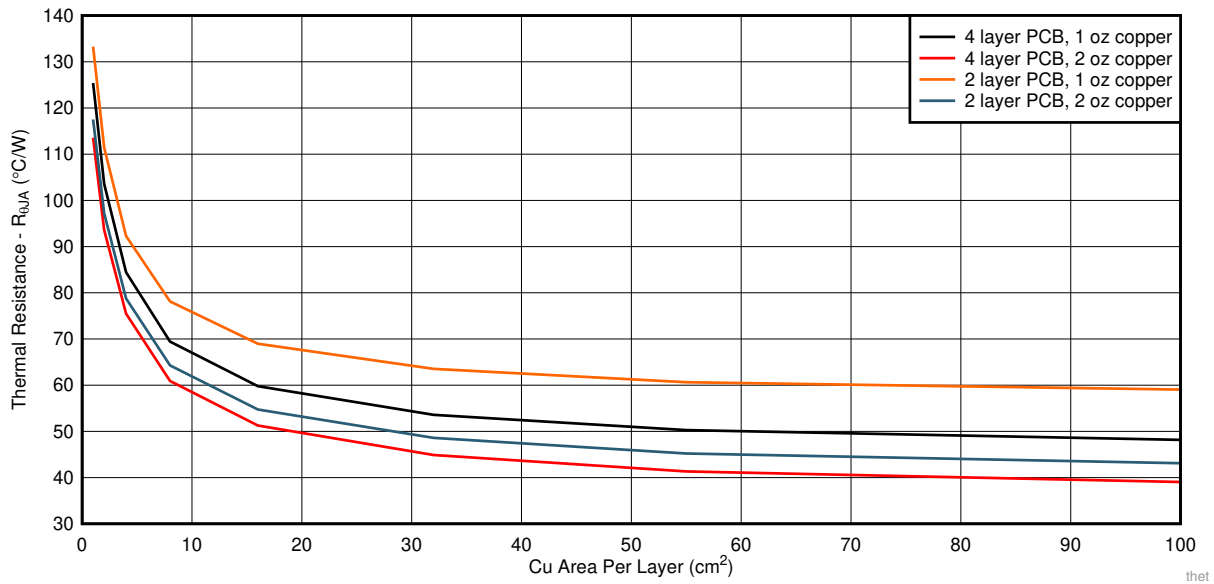
$$T_J = T_A + R_{\theta JA} \times P_D \quad (2)$$

$$I_{OUT} = (T_J - T_A) / [R_{\theta JA} \times (V_{IN} - V_{OUT})] \quad (3)$$

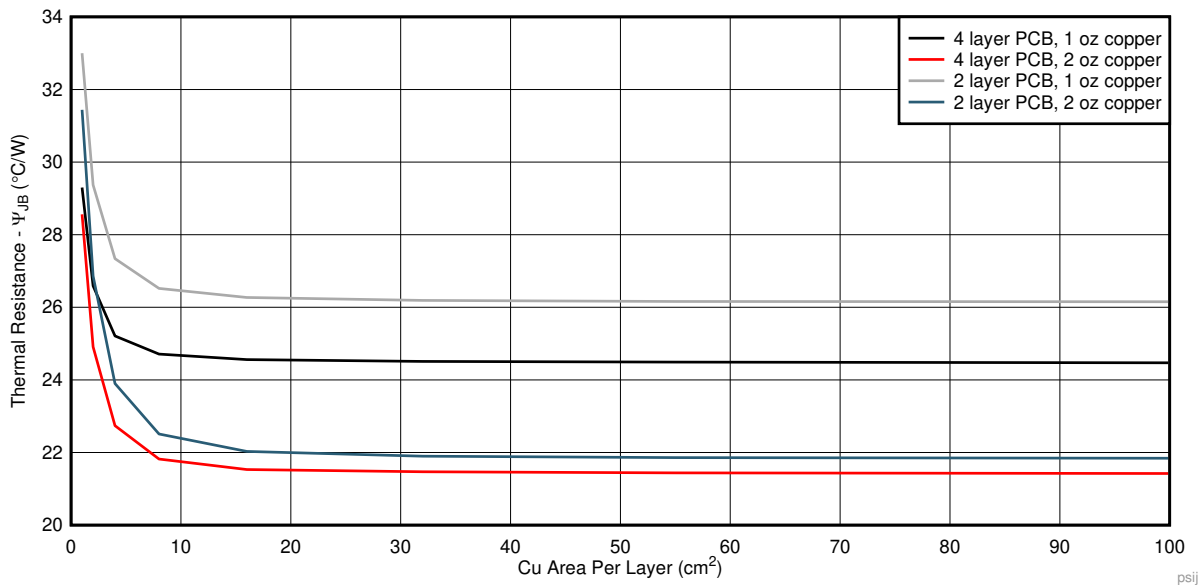
Unfortunately, this thermal resistance ($R_{\theta JA}$) is highly dependent on the heat-spreading capability built into the particular PCB design, and therefore varies according to the total copper area, copper weight, and location of the planes. The $R_{\theta JA}$ recorded in the [Thermal Information](#) table is determined by the JEDEC standard, PCB, and copper-spreading area, and is only used as a relative measure of package thermal performance. For a well-designed thermal layout, $R_{\theta JA}$ is actually the sum of the package junction-to-case (bottom) thermal resistance ($R_{\theta JCbot}$) plus the thermal resistance contribution by the PCB copper.

[图 25](#) through [图 28](#) illustrate the functions of $R_{\theta JA}$ and ψ_{JB} versus copper area and thickness. These plots are generated with a 101.6-mm x 101.6-mm x 1.6-mm PCB of two and four layers. For the four-layer board, inner planes use a 1-oz copper thickness. Outer layers are simulated with both 1-oz and 2-oz copper thicknesses. A 2 x 1 array of thermal vias with a 300- μ m drill diameter and a 25- μ m copper (Cu) plating is located beneath the thermal pad of the device. The thermal vias connect the top layer, the bottom layer and, in the case of the 4-layer board, the first inner GND plane. The copper plane of each layer is of an equal area.

Application Information (continued)

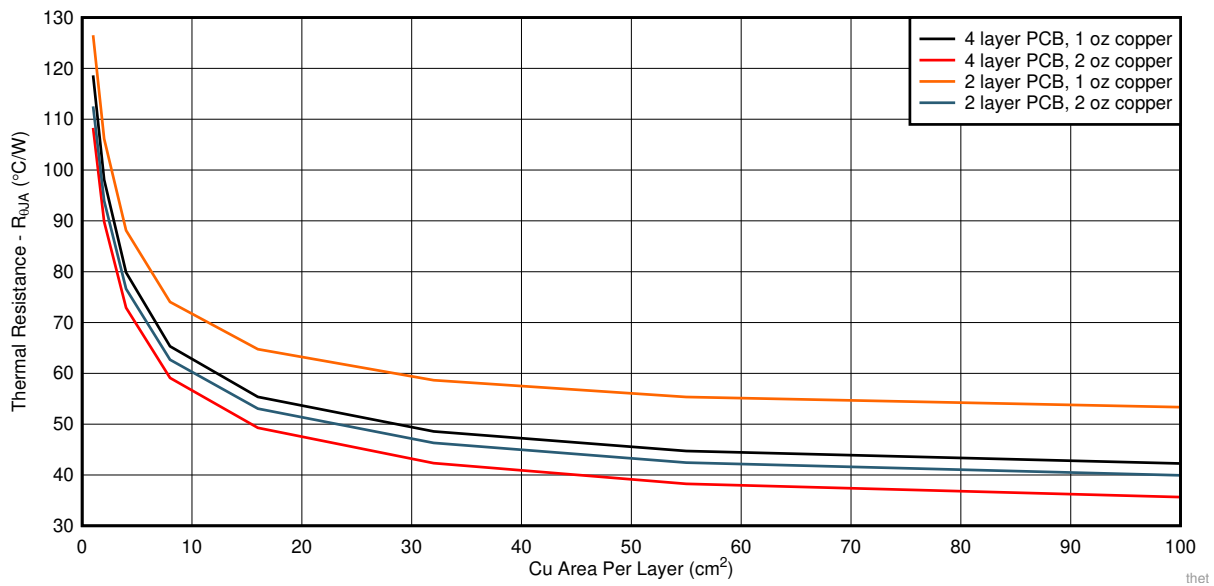


25. $R_{\theta JA}$ versus Cu Area for the WSON (DRV) Package

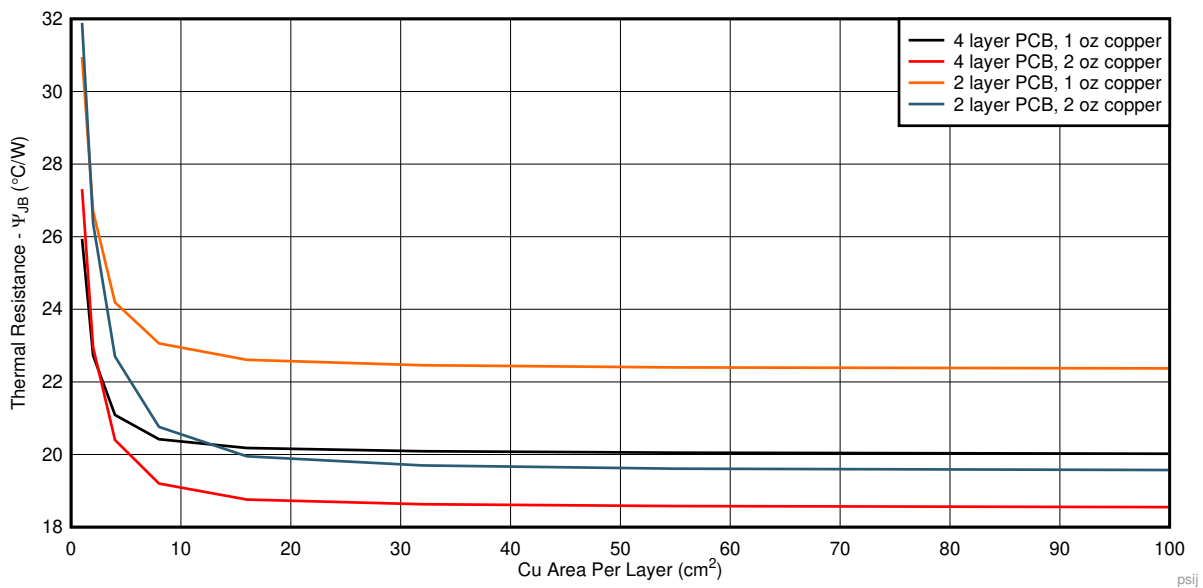


26. ψ_{JB} versus Cu Area for the WSON (DRV) Package

Application Information (continued)



27. $R_{\theta JA}$ versus Cu Area for the HVSSOP (DGN) Package



28. ψ_{JB} versus Cu Area for the HVSSOP (DGN) Package

Application Information (continued)

8.1.1.1 Estimating Junction Temperature

The JEDEC standard now recommends the use of psi (Ψ) thermal metrics to estimate the junction temperatures of the LDO when in-circuit on a typical PCB board application. These metrics are not strictly speaking thermal resistance, but rather offer practical and relative means of estimating junction temperatures. These psi metrics are determined to be significantly independent of the copper-spreading area. The key thermal metrics (Ψ_{JT} and Ψ_{JB}) are used in accordance with 式 4 and given in the *Thermal Information* table.

$$\Psi_{JT}: T_J = T_T + \Psi_{JT} \times P_D$$

$$\Psi_{JB}: T_J = T_B + \Psi_{JB} \times P_D$$

where:

- P_D is the power dissipated as explained in 式 1
- T_T is the temperature at the center-top of the device package
- T_B is the PCB surface temperature measured 1 mm from the device package and centered on the package edge

(4)

8.2 Typical Application

图 29 shows a typical application circuit for the TPS7B81. Different external component values can be used, depending on the end application. An application may require a larger output capacitor during fast load steps to prevent a large drop on the output voltage. TI recommends using a low-equivalent series resistance (ESR) ceramic capacitor with an X5R- or X7R-type dielectric.

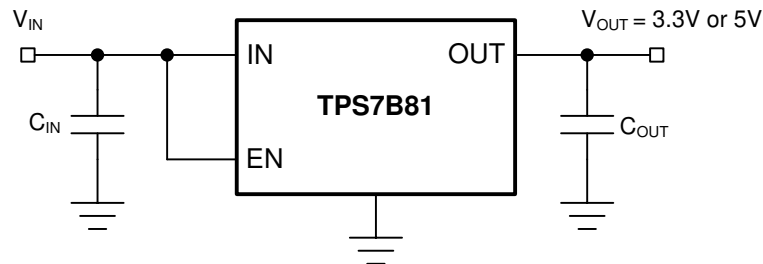


图 29. Typical Application Schematic

8.2.1 Design Requirements

Use the parameters listed in 表 2 for this design example.

表 2. Design Requirements Parameters

PARAMETER	VALUE
Input voltage range	3 V to 40 V
Output voltage	5 V or 3.3 V
Output current	150 mA maximum

8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
- Output voltage
- Output current

8.2.2.1 Input Capacitor

Although an input capacitor is not required for stability, good analog design practice is to connect a 10- μ F to 22- μ F capacitor from IN to GND. This capacitor counteracts reactive input sources and improves transient response, input ripple rejection, and PSRR. The voltage rating must be greater than the maximum input voltage.

8.2.2.2 Output Capacitor

To ensure the stability of the TPS7B81, the device requires an output capacitor with a value in the range from 1 μF to 200 μF and with an ESR range between 0.001 Ω and 5 Ω . TI recommends selecting a ceramic capacitor with low ESR to improve the load transient response.

8.2.3 Application Curve

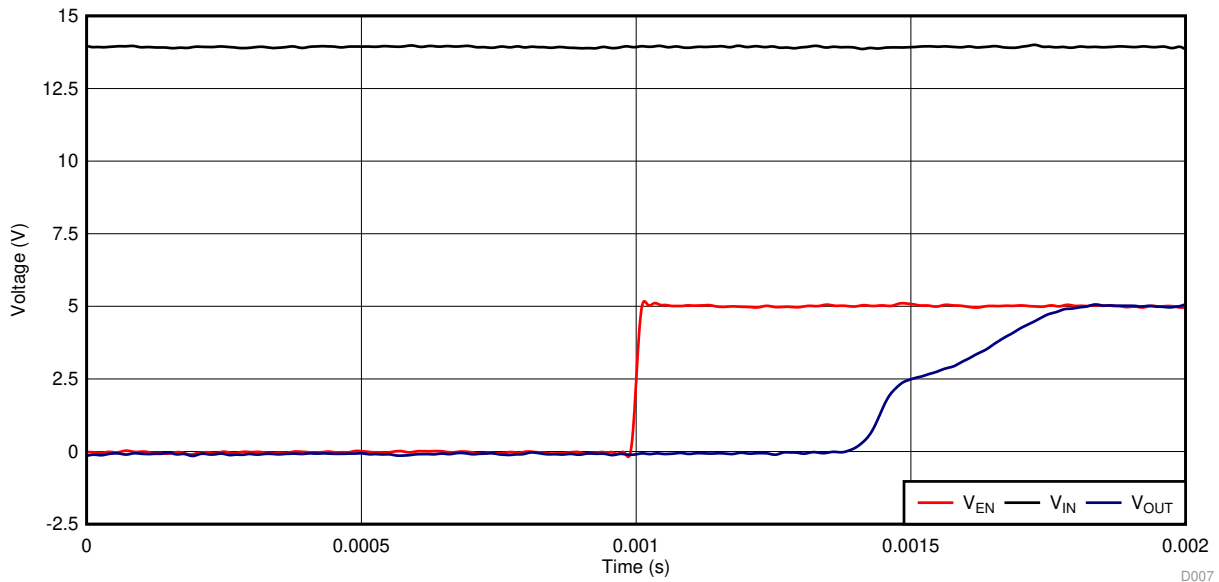


图 30. Power-Up Waveform (5 V)

9 Power Supply Recommendations

The device is designed to operate from an input voltage supply range from 3 V to 40 V. The input supply must be well regulated. If the input supply is located more than a few inches from the TPS7B81, TI recommends adding a capacitor with a value greater than or equal to 10 μF with a 0.1- μF bypass capacitor in parallel at the input.

10 Layout

10.1 Layout Guidelines

Layout is an important step for LDO power supplies, especially for high-voltage and large output current supplies. If the layout is not carefully designed, the regulator can fail to deliver enough output current because of thermal limitations. To improve the thermal performance of the device, and to maximize the current output at high ambient temperature, spread the copper under the thermal pad as far as possible and put enough thermal vias on the copper under the thermal pad. [Figure 31](#) shows an example layout.

10.2 Layout Example

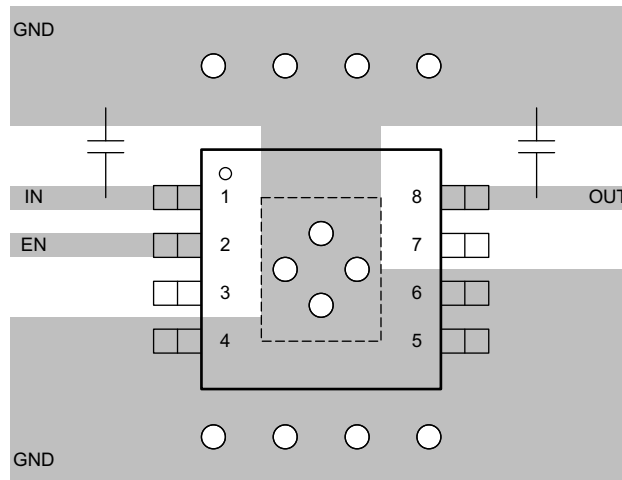


Figure 31. Example Layout Diagram

11 デバイスおよびドキュメントのサポート

11.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の「アラートを受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

11.2 サポート・リソース

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

11.3 商標

PowerPAD, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

11.4 静電気放電に関する注意事項



すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

11.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS7B8133DGNR	Active	Production	HVSSOP (DGN) 8	2500 LARGE T&R	Yes	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	26BX
TPS7B8133DGNR.A	Active	Production	HVSSOP (DGN) 8	2500 LARGE T&R	Yes	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	26BX
TPS7B8133DRVR	Active	Production	WSON (DRV) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	26DH
TPS7B8133DRVR.A	Active	Production	WSON (DRV) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	26DH
TPS7B8150DGNR	Active	Production	HVSSOP (DGN) 8	2500 LARGE T&R	Yes	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	26CX
TPS7B8150DGNR.A	Active	Production	HVSSOP (DGN) 8	2500 LARGE T&R	Yes	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	26CX
TPS7B8150DRVR	Active	Production	WSON (DRV) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	26EH
TPS7B8150DRVR.A	Active	Production	WSON (DRV) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	26EH

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TPS7B81 :

- Automotive : [TPS7B81-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

GENERIC PACKAGE VIEW

DRV 6

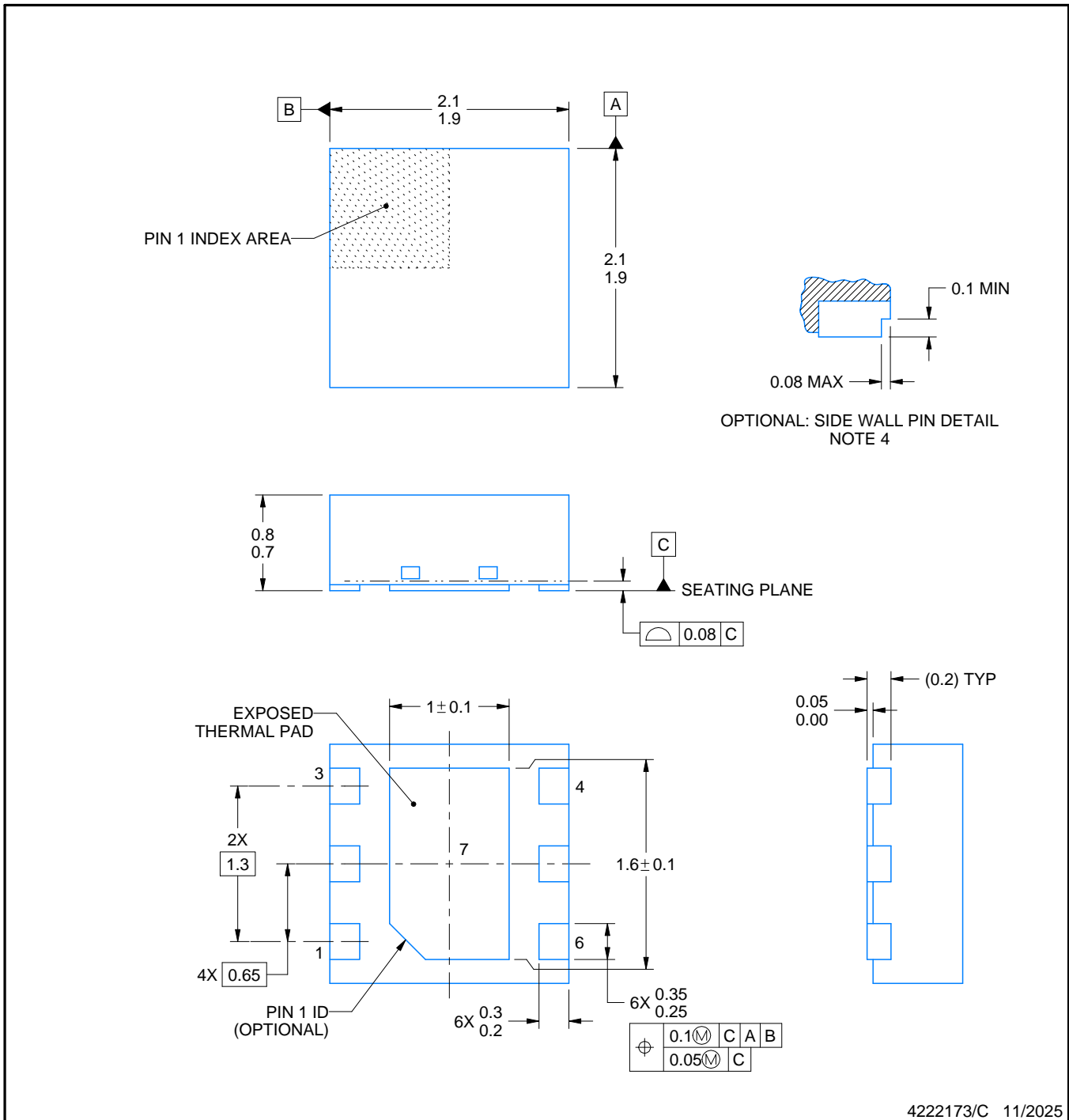
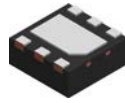
WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4206925/F



NOTES:

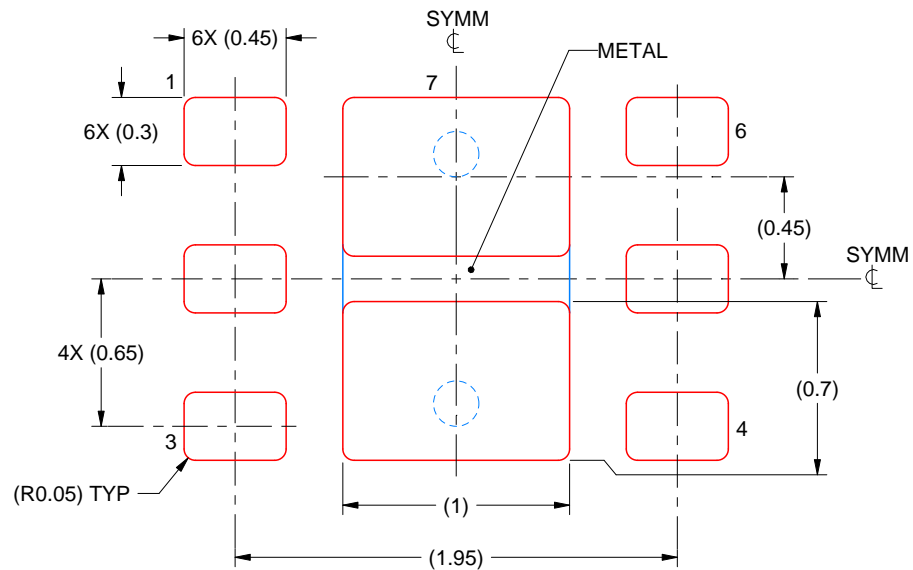
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
4. Minimum 0.1 mm solder wetting on pin side wall. Available for wettable flank version only.

EXAMPLE STENCIL DESIGN

DRV0006A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD #7
88% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:30X

4222173/C 11/2025

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

GENERIC PACKAGE VIEW

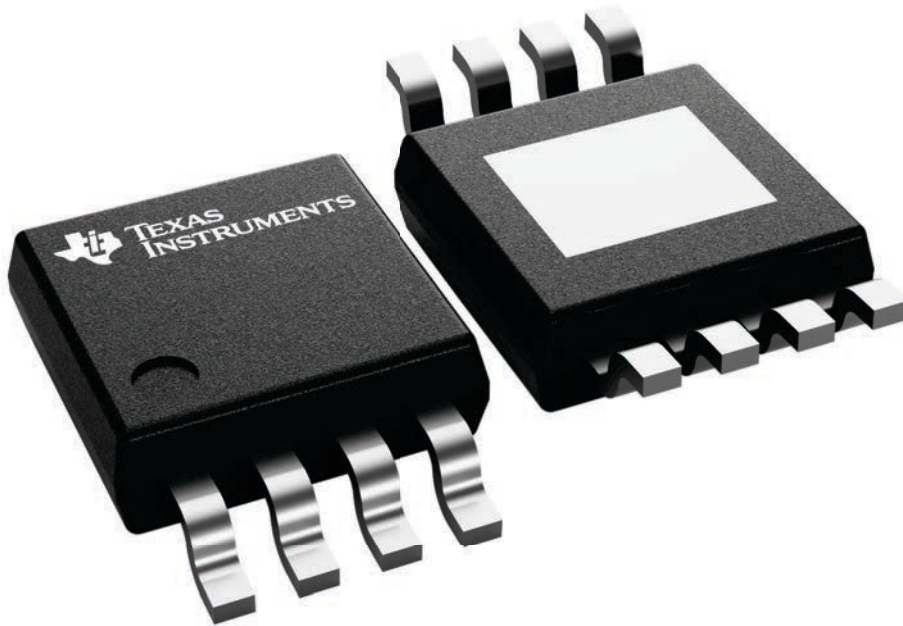
DGN 8

PowerPAD™ HVSSOP - 1.1 mm max height

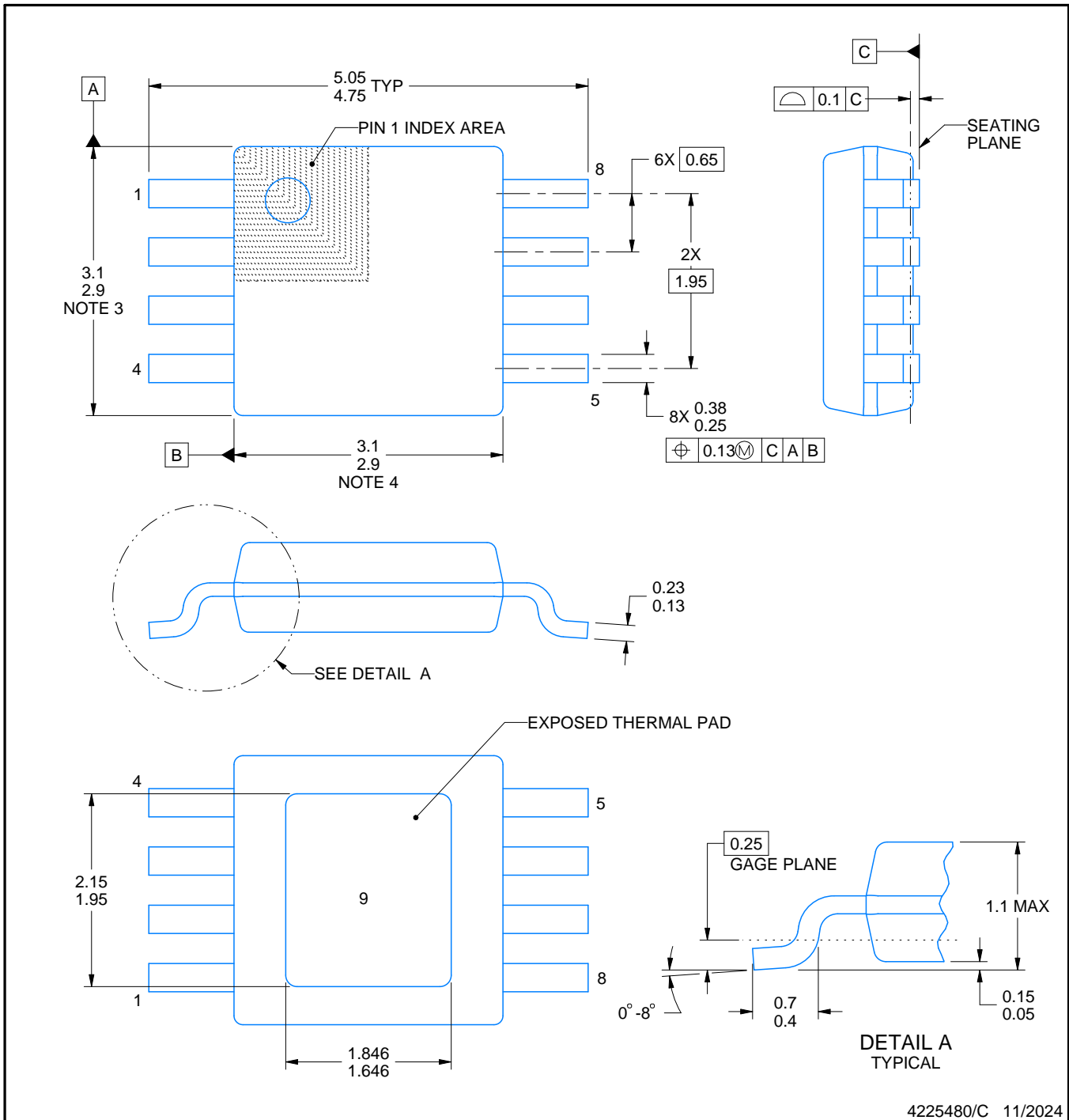
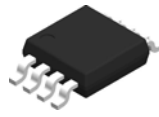
3 x 3, 0.65 mm pitch

SMALL OUTLINE PACKAGE

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4225482/B



4225480/C 11/2024

NOTES:

PowerPAD is a trademark of Texas Instruments.

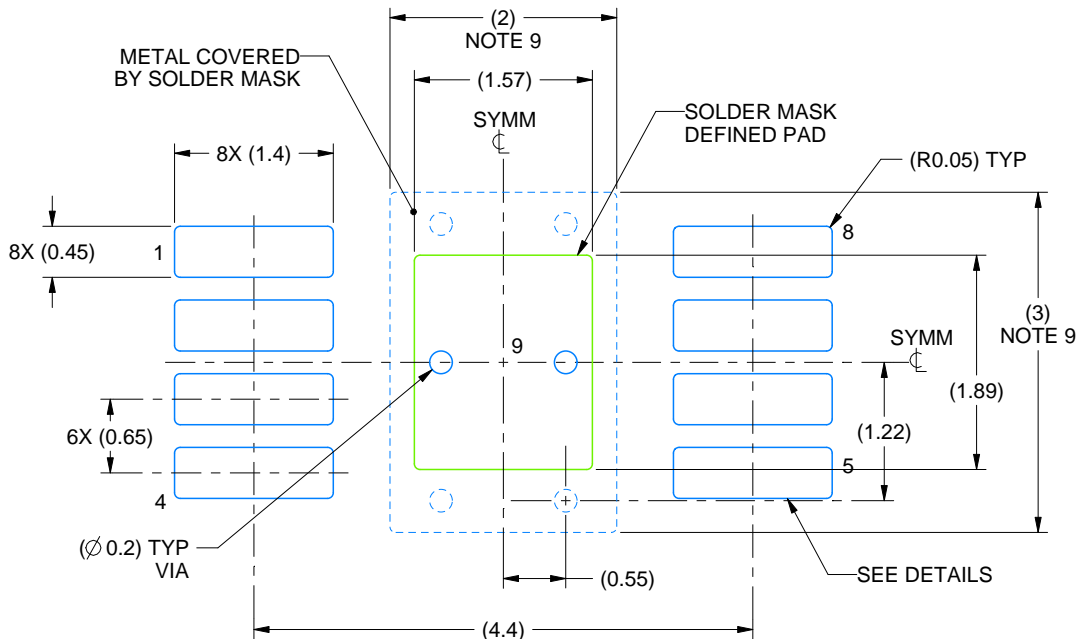
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

EXAMPLE BOARD LAYOUT

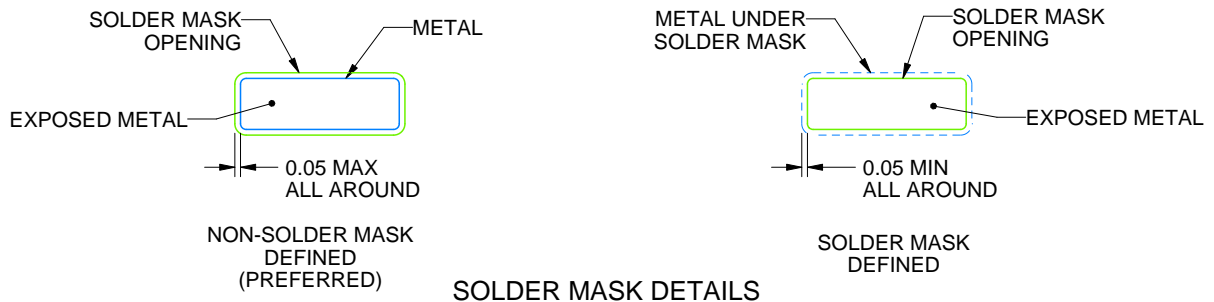
DGN0008G

PowerPAD™ HVSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 15X



4225480/C 11/2024

NOTES: (continued)

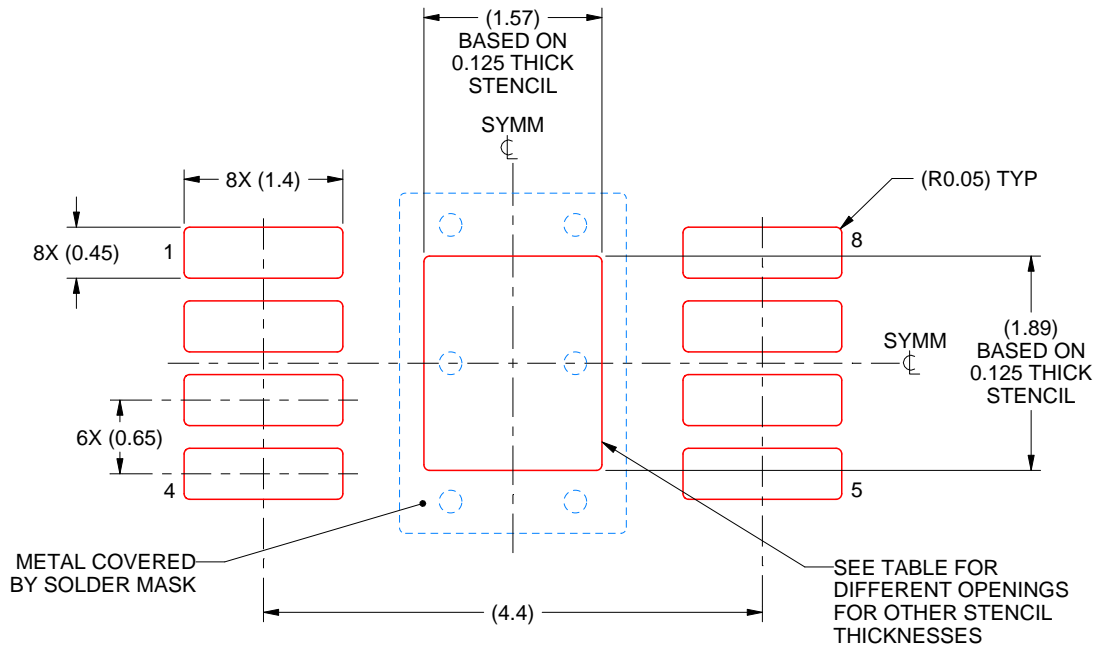
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.

EXAMPLE STENCIL DESIGN

DGN0008G

PowerPAD™ HVSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
 EXPOSED PAD 9:
 100% PRINTED SOLDER COVERAGE BY AREA
 SCALE: 15X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	1.76 X 2.11
0.125	1.57 X 1.89 (SHOWN)
0.15	1.43 X 1.73
0.175	1.33 X 1.60

4225480/C 11/2024

NOTES: (continued)

10. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
11. Board assembly site may have different recommendations for stencil design.

重要なお知らせと免責事項

TI は、技術データと信頼性データ (データシートを含みます)、設計リソース (リファレンス デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、TI 製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した TI 製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとし、

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている TI 製品を使用するアプリケーションの開発の目的でのみ、TI はその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。TI や第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、TI およびその代理人を完全に補償するものとし、TI は一切の責任を拒否します。

TI の製品は、[TI の販売条件](#)、[TI の総合的な品質ガイドライン](#)、[ti.com](#) または TI 製品などに関連して提供される他の適用条件に従い提供されます。TI がこれらのリソースを提供することは、適用される TI の保証または他の保証の放棄の拡大や変更を意味するものではありません。TI がカスタム、またはカスタマー仕様として明示的に指定していない限り、TI の製品は標準的なカタログに掲載される汎用機器です。

お客様がいかなる追加条項または代替条項を提案する場合も、TI はそれらに異議を唱え、拒否します。

Copyright © 2026, Texas Instruments Incorporated

最終更新日 : 2025 年 10 月